

具有可调频率的 LM21215 2.95V 至 5.5V、12A、电压模式同步降压稳压器

1 特性

- 集成 7mΩ 高侧和 4.3mΩ 低侧 FET 开关
- 可调节电流限制
- 可调输出电压范围为 0.6V 至 V_{IN} （支持 100% 占空比），基准为 $\pm 1\%$
- 输入电压范围为 2.95V 至 5.5V
- 500kHz 固定开关频率
- 启动至预偏置负载
- 输出电压跟踪功能
- 高带宽电压环路误差放大器
- 通过外部电容器进行可调软启动
- 具有迟滞功能的精密使能引脚
- 集成 OVP、OTP、UVLO 和电源正常状态
- 热增强型 20 引脚 HTSSOP 外露焊盘封装
- 使用 LM21215 并借助 WEBENCH® 电源设计器创建定制设计方案

2 应用

- 宽带、网络和无线通信
- 高性能 FPGA、ASIC 和微处理器
- 通过 5V 或 3.3V 总线实现轻松设计和高效负载点调节

3 说明

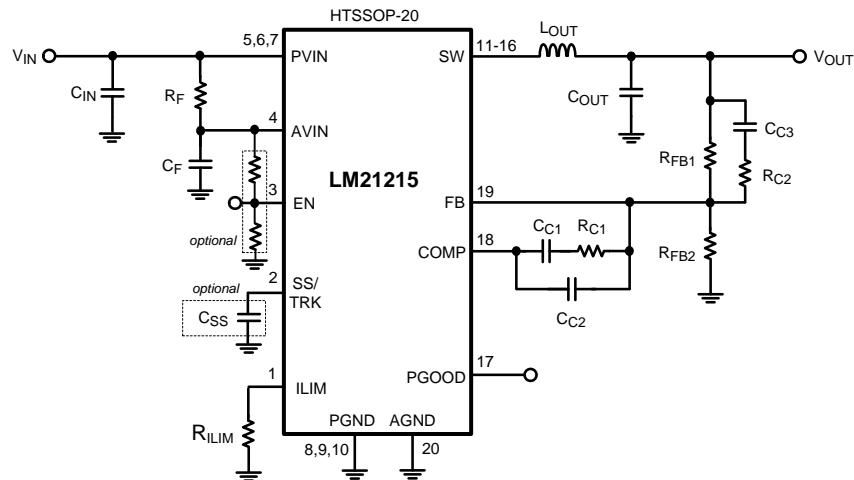
LM21215 是一款单片同步负载点降压稳压器，能够提供高达 15A 的持续输出电流，同时以出色的效率产生低至 0.6V 的输出电压。该器件经过优化，可在 2.95V 至 5.5V 的输入电压范围内工作，因此适合各种低电压系统。电压模式控制环路可提供高噪声抗扰度、低占空比能力，并且可通过任何类型的输出电容补偿至稳定状态，从而提供最大的灵活性和易用性。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
LM21215	HTSSOP (20)	6.50mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化应用电路



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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision E (March 2013) to Revision F	Page
• 仅有编辑更改，无技术性修订；添加了 WEBENCH 链接	1

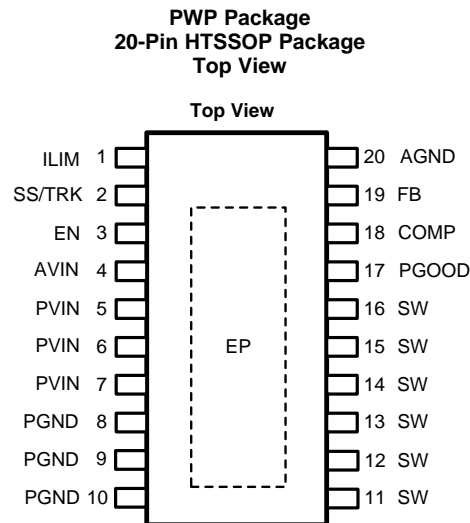
Changes from Revision D (March 2013) to Revision E	Page
• 已更改 将美国国家半导体数据表的布局更改为 TI 格式	1

5 说明（续）

LM21215 特性 内部过压保护 (OVP) 和电阻器可编程过流保护 (OCP)，可提高系统可靠性。精密使能引脚和集成 UVLO 支持对器件的开启进行严格的控制和定序。启动浪涌电流受内部固定和外部可调的软启动电路限制。借助集成电源正常状态电路，可实现故障检测和电源定序。

LM21215 设计 用于在多轨电源架构中良好运行。可使用 **SS/TRK** 引脚将该器件的输出电压配置为跟踪外部电压轨。如果在启动时对输出进行预偏置，则不会灌入电流，从而使输出电压平稳上升，超过预偏置电压。该稳压器采用具有外露焊盘的 20 引脚 **HTSSOP** 封装，该焊盘可焊接至 **PCB**，因而不需大型散热装置。

6 Pin Configuration and Functions



Pin Functions

PIN		
NO.	NAME	DESCRIPTION
1	ILIM	Resistor-programmable current limit pin. A resistor connected to this pin and ground will set the value of the rising current limit I_{CLR} . Shorting this pin to AGND programs the device to the maximum possible current limit.
2	SS/TRK	Soft-start control pin. An internal 2- μ A current source charges an external capacitor connected between this pin and AGND to set the output voltage ramp rate during startup. This pin can also be used to configure the tracking feature.
3	EN	Active high enable input for the device. If not used, the EN pin can be left open, which will go high due to an internal current source.
4	AVIN	Analog input voltage supply that generates the internal bias. It is recommended to connect PVIN to AVIN through a low pass RC filter to minimize the influence of input rail ripple and noise on the analog control circuitry.
5,6,7	PVIN	Input voltage to the power switches inside the device. These pins should be connected together at the device. A low ESR input capacitance should be located as close as possible to these pins.
8,9,10	PGND	Power ground pins for the internal power switches.
11-16	SW	Switch node pins. These pins should be tied together locally and connected to the filter inductor.
17	PGOOD	Open-drain power good indicator.
18	COMP	Compensation pin is connected to the output of the voltage loop error amplifier.
19	FB	Feedback pin is connected to the inverting input of the voltage loop error amplifier.
20	AGND	Quiet analog ground for the internal reference and bias circuitry.
EP	Exposed Pad	Exposed metal pad on the underside of the package with an electrical and thermal connection to PGND. TI recommends connecting this pad to the PC board ground plane in order to improve thermal dissipation.

7 Specifications

7.1 Absolute Maximum Ratings

See

PVIN ⁽¹⁾ , AVIN to GND	–0.3V to +6V
SW ⁽²⁾ , EN, FB, COMP, PGOOD, SS/TRK to GND	–0.3V to PVIN + 0.3V
Storage Temperature	–65°C to 150°C
Lead Temperature (Soldering, 10 sec.)	260°C

- (1) The PVIN pin can tolerate transient voltages up to 6.5 V for a period of up to 6 ns. These transients can occur during the normal operation of the device.
- (2) The SW pin can tolerate transient voltages up to 9.0 V for a period of up to 6 ns, and –1 V for a duration of 4 ns. These transients can occur during the normal operation of the device.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Ratings

See ⁽¹⁾

PVIN, AVIN to GND	+2.95V to +5.5V
Junction Temperature	–40°C to +125°C
θ _{JA} ⁽²⁾	24°C/W

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended operating ratings indicate conditions for which the device is intended to be functional, but do not ensure specific performance limits. For ensured specifications and test conditions, see the *Electrical Characteristics*.
- (2) Thermal measurements were performed on a 2 × 2 inch, 4-layer, 2 oz. copper outer layer, 1 oz. copper inner layer board with twelve 8 mil. vias under the EP of the device and an additional sixteen 8 mil. vias under the unexposed package.

7.4 Electrical Characteristics

Unless otherwise stated, the following conditions apply: V_{PVIN, AVIN} = 5V. Limits in standard type are for T_J = 25°C only, limits in **boldface type** apply over the junction temperature (T_J) range of –40°C to +125°C. Minimum and maximum limits are specified through test, design, or statistical correlation. Typical values represent the most likely parametric norm at T_J = 25°C, and are provided for reference purposes only.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SYSTEM						
V _{FB}	Feedback pin voltage	V _{IN} = 2.95V to 5.5V	-1%	0.6	1%	V
ΔV _{OUT} /ΔI _{OUT}	Load Regulation			0.02		%V _{OUT} /A
ΔV _{OUT} /ΔV _{IN}	Line Regulation			0.1		%V _{OUT} /V
R _{DS(on) HS}	High Side Switch On Resistance	I _{SW} = 12A		7	9.0	mΩ
R _{DS(on) LS}	Low Side Switch On Resistance	I _{SW} = 12A		4.3	6.0	mΩ
I _{CLR}	HS Rising Switch Current Limit	R _{ILIM} = 16.5 kΩ	16.5	20	23.5	A
		R _{ILIM} = 41.3 kΩ	8.5	10	11.5	
		R _{ILIM} = 130 kΩ		3.8		
I _{CLF}	LS Falling Switch Current Limit	R _{ILIM} = 16.5 kΩ		14.5		A
		R _{ILIM} = 41.3 kΩ		7.5		
		R _{ILIM} = 130 kΩ		3		
V _{ZX}	Zero Cross Voltage		-8	3	12	mV
I _Q	Operating Quiescent Current			1.5	3	mA
I _{SD}	Shutdown Quiescent Current	V _{EN} = 0V		50	70	μA
V _{UVLO}	AVIN Under Voltage Lockout	AVIN Rising	2.45	2.7	2.95	V
V _{UVLOHYS}	AVIN Under Voltage Lockout Hysteresis		140	200	280	mV

Electrical Characteristics (continued)

Unless otherwise stated, the following conditions apply: $V_{PVIN}, V_{VIN} = 5V$. Limits in standard type are for $T_J = 25^\circ C$ only, limits in **boldface type** apply over the junction temperature (T_J) range of $-40^\circ C$ to $+125^\circ C$. Minimum and maximum limits are specified through test, design, or statistical correlation. Typical values represent the most likely parametric norm at $T_J = 25^\circ C$, and are provided for reference purposes only.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SYSTEM						
$V_{TRACKOS}$	SS/TRACK PIN accuracy ($V_{SS} - V_{FB}$)	$0 < V_{TRACK} < 0.55V$	-10	6	20	mV
I_{SS}	Soft-Start Pin Source Current		1.3	1.9	2.5	μA
t_{INTSS}	Internal Soft-Start Ramp to Vref	$C_{SS} = 0$	350	500	675	μs
$t_{RESETSS}$	Device reset to soft-start ramp		50	110	200	μs
OSCILLATOR						
f_{OSC}	Switching Frequency		475	500	525	kHz
$t_{HSBLANK}$	HS OCP blanking time	Rising edge of SW to I_{CLR} comparison		55		ns
$t_{LSBLANK}$	LS OCP blanking time	Falling edge of SW to I_{CLF} comparison		400		ns
$t_{ZXBLANK}$	Zero Cross blanking time	Falling edge of SW to V_{ZX} comparison		120		ns
t_{MINON}	Minimum HS on-time			140		ns
ΔV_{RAMP}	PWM Ramp p-p Voltage			0.8		V
ERROR AMPLIFIER						
V_{OL}	Error Amplifier Open Loop Voltage Gain	$I_{COMP} = -65\mu A$ to 1mA		95		dBV/V
GBW	Error Amplifier Gain-Bandwidth Product			11		MHz
I_{FB}	Feedback Pin Bias Current	$V_{FB} = 0.6V$		1		nA
$I_{COMPSRC}$	COMP Output Source Current			1		mA
$I_{COMPSINK}$	COMP Output Sink Current			65		μA
POWERGOOD						
V_{OVP}	Overvoltage Protection Rising Threshold	V_{FB} Rising	105	112.5	120	$\%V_{FB}$
V_{OVPHYS}	Overvoltage Protection Hysteresis	V_{FB} Falling		2		$\%V_{FB}$
V_{UVP}	Undervoltage Protection Rising Threshold	V_{FB} Rising	82	90	97	$\%V_{FB}$
V_{UVPHYS}	Undervoltage Protection Hysteresis	V_{FB} Falling		2.5		$\%V_{FB}$
t_{PGDGL}	PGOOD Deglitch Low (OVP/UVP Condition Duration to PGOOD Falling)			15		μs
t_{PGDGH}	PGOOD Deglitch High (minimum low pulse)			12		μs
R_{PD}	PGOOD Pulldown Resistance		10	20	40	Ω
$I_{PGOODLEAK}$	PGOOD Leakage Current	$V_{PGOOD} = 5V$		1		nA
LOGIC						
V_{IHENR}	EN Pin Rising Threshold	V_{EN} Rising	1.20	1.35	1.45	V
V_{ENHYS}	EN Pin Hysteresis		50	110	180	mV
I_{EN}	EN Pin Pullup Current	$V_{EN} = 0V$		2		μA
THERMAL SHUTDOWN						
$T_{THERMSD}$	Thermal Shutdown			165		$^\circ C$
$T_{THERMSDHYS}$	Thermal Shutdown Hysteresis			10		$^\circ C$

7.5 Typical Characteristics

Unless otherwise specified: $V_{IN} = 5\text{ V}$, $V_{OUT} = 1.2\text{ V}$, $L = 0.56\text{ }\mu\text{H}$ ($1.8\text{-m}\Omega\text{ }R_{DCR}$), $C_{SS} = 33\text{ nF}$, $T_A = 25^\circ\text{C}$ for efficiency curves, loop gain plots and waveforms, and $T_J = 25^\circ\text{C}$ for all others.

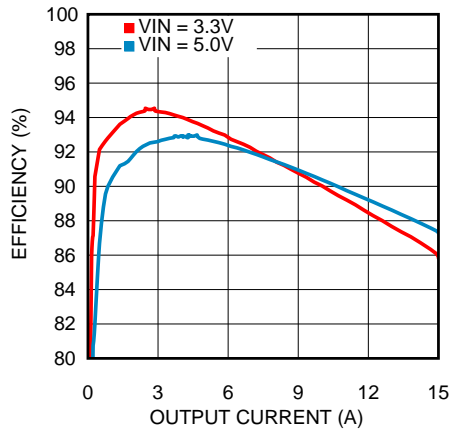
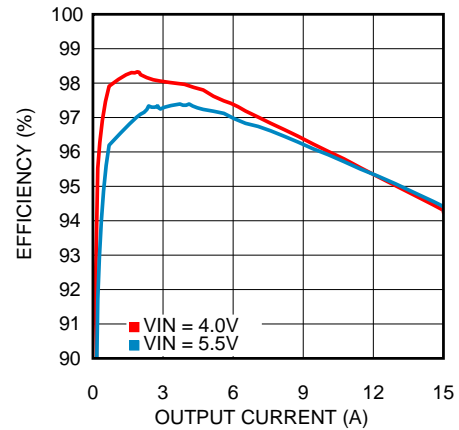


Figure 1. Efficiency



$V_{OUT} = 3.3\text{ V}$

Inductor P/N SER2010-02MLD

Figure 2. Efficiency

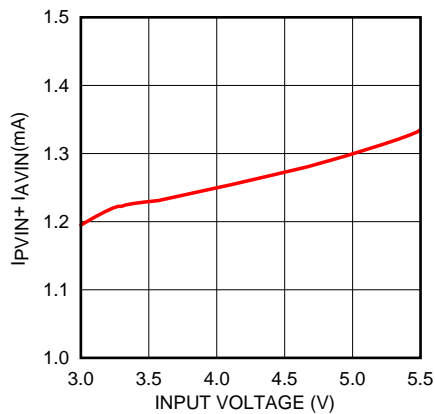


Figure 3. Non-Switching I_{QTOTAL} vs V_{IN}

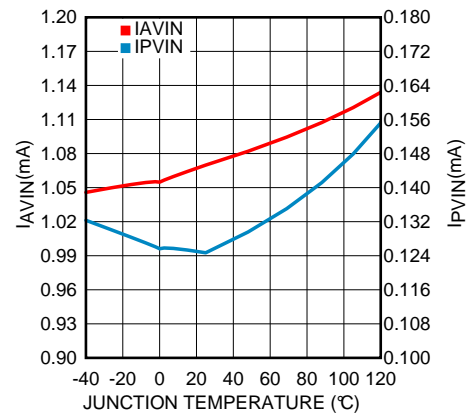


Figure 4. Non-Switching I_{AVIN} and I_{PVIN} vs Temperature

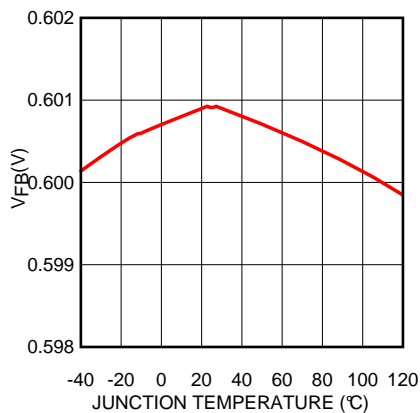


Figure 5. V_{FB} vs Temperature

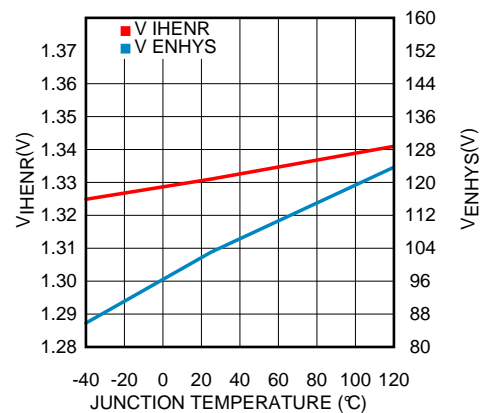


Figure 6. Enable Threshold and Hysteresis vs Temperature

Typical Characteristics (continued)

Unless otherwise specified: $V_{IN} = 5\text{ V}$, $V_{OUT} = 1.2\text{ V}$, $L = 0.56\text{ }\mu\text{H}$ ($1.8\text{-m}\Omega\text{ }R_{DCR}$), $C_{SS} = 33\text{ nF}$, $T_A = 25^\circ\text{C}$ for efficiency curves, loop gain plots and waveforms, and $T_J = 25^\circ\text{C}$ for all others.

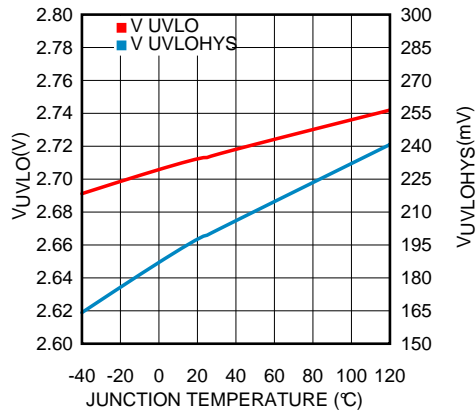


Figure 7. UVLO Threshold and Hysteresis vs Temperature

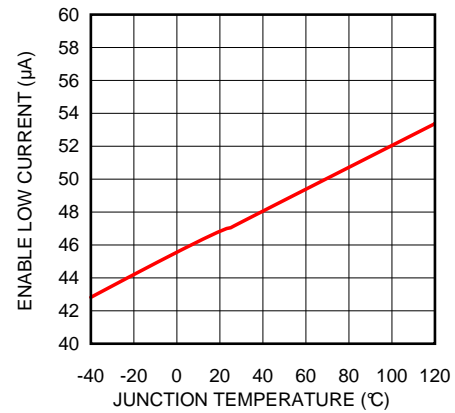


Figure 8. Enable Low Current vs Temperature

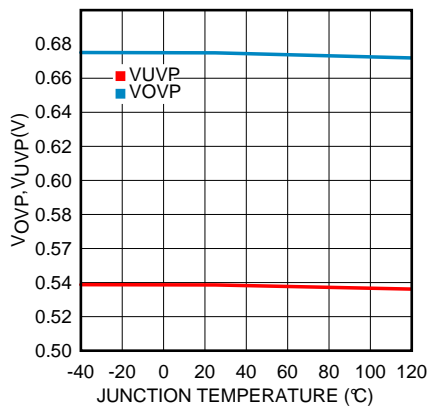


Figure 9. OVP/UVP Threshold vs Temperature

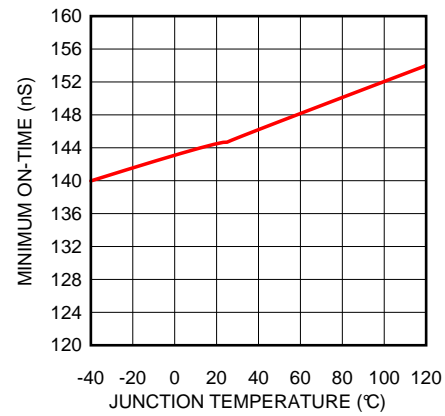


Figure 10. Minimum On-Time vs Temperature

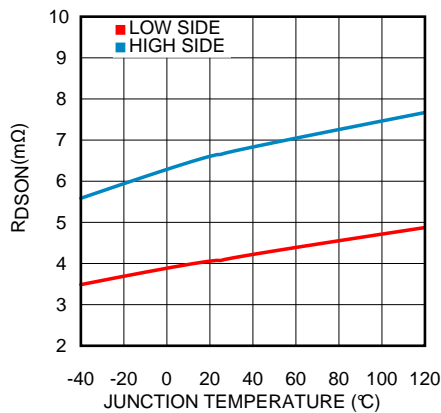


Figure 11. FET Resistance vs Temperature

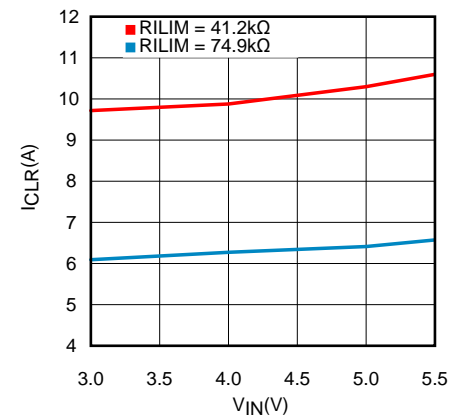


Figure 12. Peak Current Limit (I_{CLR}) vs V_{IN}

Typical Characteristics (continued)

Unless otherwise specified: $V_{IN} = 5\text{ V}$, $V_{OUT} = 1.2\text{ V}$, $L = 0.56\text{ }\mu\text{H}$ ($1.8\text{-m}\Omega\text{ }R_{DCR}$), $C_{SS} = 33\text{ nF}$, $T_A = 25^\circ\text{C}$ for efficiency curves, loop gain plots and waveforms, and $T_J = 25^\circ\text{C}$ for all others.

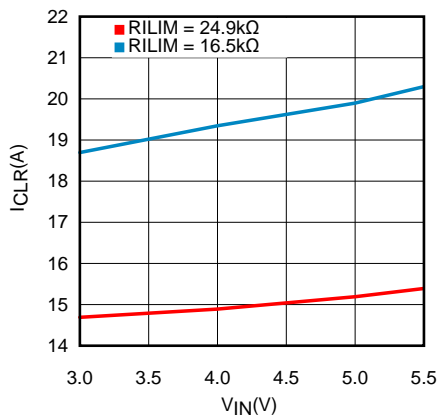
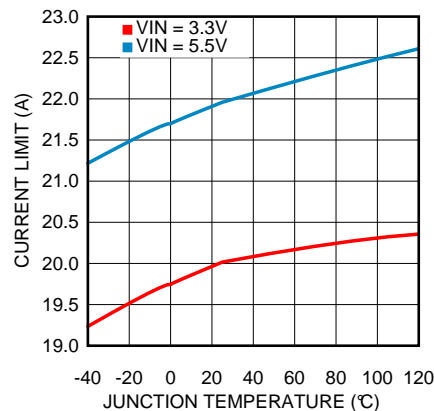
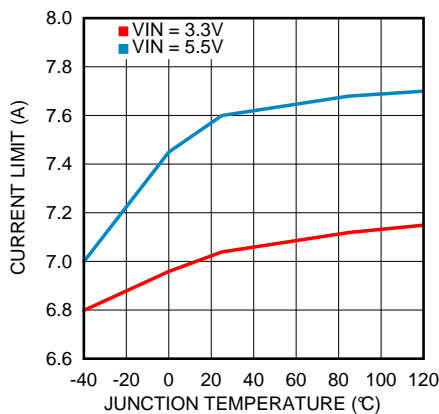


Figure 13. Peak Current Limit (I_{CLR}) vs V_{IN}



$R_{ILIM} = 10\text{ K}\Omega$

Figure 14. Peak Current Limit (I_{CLR}) vs Temperature



$R_{ILIM} = 61.9\text{ K}\Omega$

Figure 15. Peak Current Limit (I_{CLR}) vs Temperature

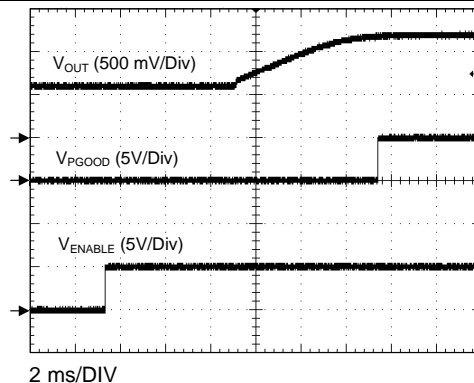


Figure 16. Start-up With Prebiased Output

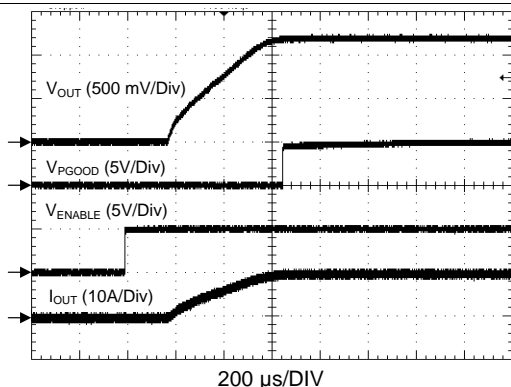


Figure 17. Start-up With SS/TRK Open Circuit

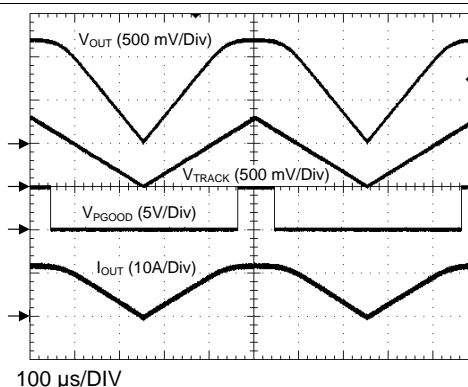


Figure 18. Start-up With Applied Track Signal

Typical Characteristics (continued)

Unless otherwise specified: $V_{IN} = 5\text{ V}$, $V_{OUT} = 1.2\text{ V}$, $L = 0.56\text{ }\mu\text{H}$ ($1.8\text{-m}\Omega\text{ }R_{DCR}$), $C_{SS} = 33\text{ nF}$, $T_A = 25^\circ\text{C}$ for efficiency curves, loop gain plots and waveforms, and $T_J = 25^\circ\text{C}$ for all others.

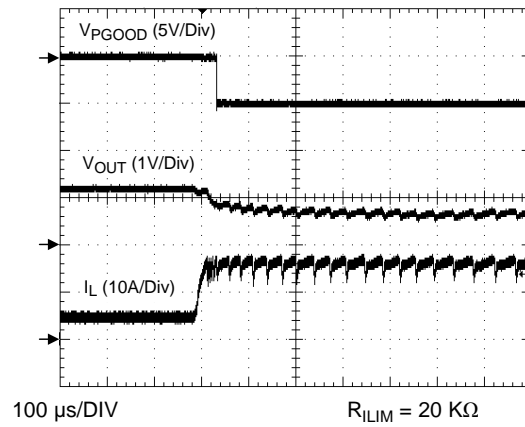


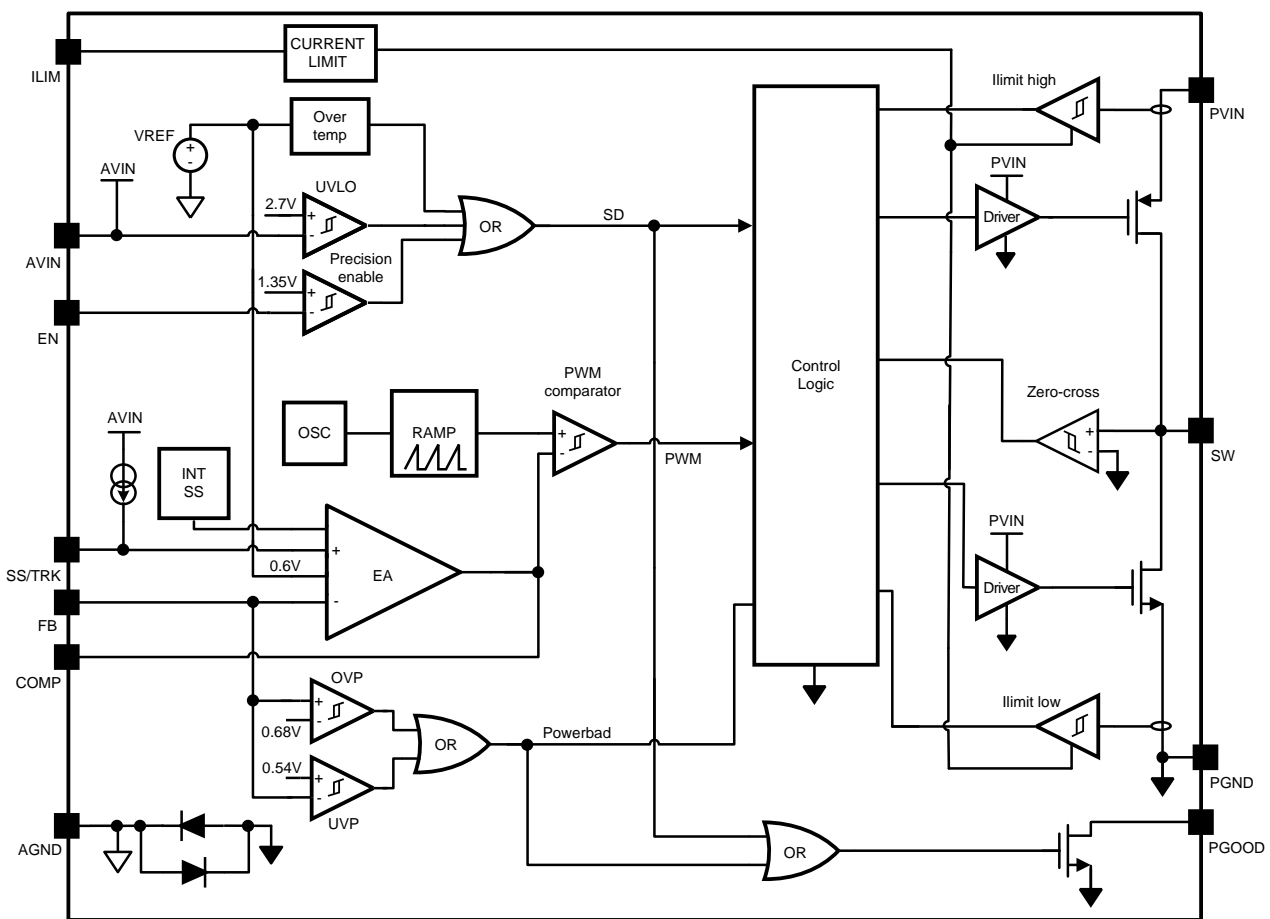
Figure 19. Output Overcurrent Condition

8 Detailed Description

8.1 Overview

The LM21215 switching regulator features all of the functions necessary to implement an efficient low voltage buck regulator using a minimum number of external components. This easy to use regulator features two integrated switches and is capable of supplying up to 15 A of continuous output current. The regulator utilizes voltage mode control with trailing edge modulation to optimize stability and transient response over the entire output voltage range. The device can operate at high switching frequency allowing use of a small inductor while still achieving high efficiency. The precision internal voltage reference allows the output to be set as low as 0.6 V. Fault protection features include: current limiting, thermal shutdown, overvoltage protection, and shutdown capability. The device is available in the 20-pin HTSSOP package featuring an exposed pad to aid thermal dissipation. The LM21215 can be used in numerous applications to efficiently step-down from a 5-V or 3.3-V bus.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Precision Enable

The enable (EN) pin allows the output of the device to be enabled or disabled with an external control signal. This pin is a precision analog input that enables the device when the voltage exceeds 1.35 V (typical). The EN pin has 110 mV of hysteresis and disables the output when the enable voltage falls below 1.24V (typical). If the EN pin is not used, it can be left open, and will be pulled high by an internal 2-μA current source. Since the enable pin has a precise turn-on threshold it can be used along with an external resistor divider network from VIN to configure the device to turn on at a precise input voltage.

Feature Description (continued)

8.3.2 UVLO

The LM21215 has a built-in undervoltage lockout protection circuit that keeps the device from switching until the input voltage reaches 2.7 V (typical). The UVLO threshold has 200 mV of hysteresis that keeps the device from responding to power-on glitches during start up. If desired the turn-on point of the supply can be changed by using the precision enable pin and a resistor divider network connected to VIN as shown in Figure 25 in the design guide.

8.3.3 Current Limit

The LM21215 has programmable current limit protection to avoid dangerous current levels through the power FETs and inductor. A current limit condition is met when the current through the high side FET exceeds the rising current limit level (I_{CLR}). The control circuitry will respond to this event by turning off the high side FET and turning on the low side FET. This forces a negative voltage on the inductor, thereby causing the inductor current to decrease. The high side FET will not conduct again until the lower current limit level (I_{CLF}) is sensed on the low side FET. At this point, the device will resume normal switching.

A current limit condition will cause the internal soft-start voltage to ramp downward. After the internal soft-start ramps below the Feedback (FB) pin voltage, (nominally 0.6 V), FB will begin to ramp downward, as well. This voltage foldback will limit the power consumption in the device, thereby protecting the device from continuously supplying power to the load under a condition that does not fall within the device SOA. After the current limit condition is cleared, the internal soft-start voltage will ramp up again. Figure 20 shows current limit behavior with V_{SS} , V_{FB} , V_{OUT} and V_{SW} .

8.3.4 Short-Circuit Protection

In the unfortunate event that the output is shorted with a low impedance to ground, the LM21215 limits the current into the short by resetting the device. A short-circuit condition is sensed by a current-limit condition coinciding with a voltage on the FB pin that is lower than 100 mV. When this condition occurs, the device begins its reset sequence, turning off both power FETs and discharging the soft-start capacitor after $t_{RESETSS}$ (nominally 110 μ s). The device will then attempt to restart. If the short-circuit condition still exists, it will reset again, and repeat until the short-circuit is cleared. The reset prevents excess current flowing through the FETs in a highly inefficient manner, potentially causing thermal damage to the device or the bus supply.

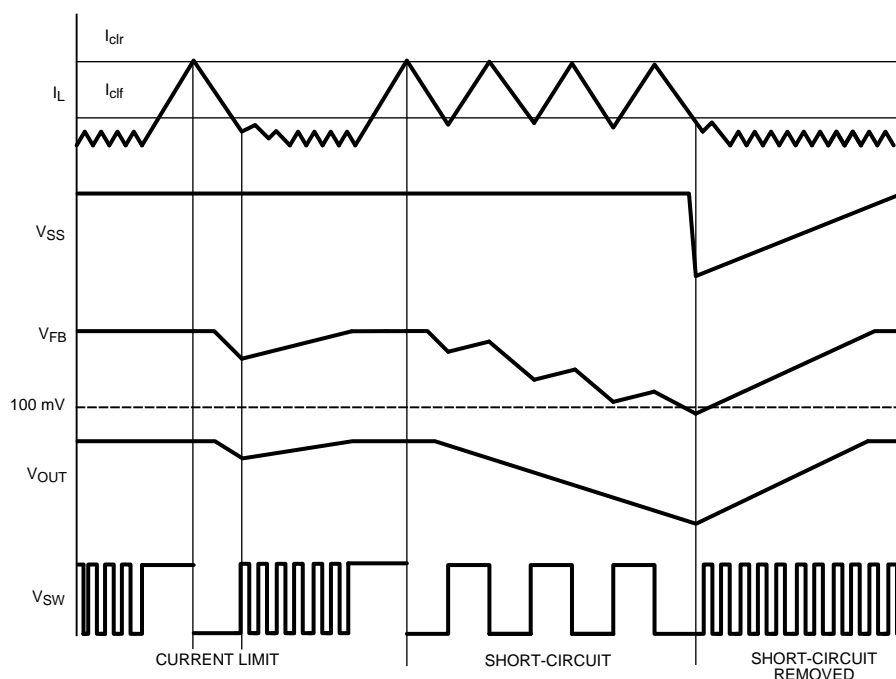


Figure 20. Current Limit Conditions

Feature Description (continued)

8.3.5 Thermal Protection

Internal thermal shutdown circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When activated, typically at 165°C, the LM21215 tri-states the power FETs and resets soft start. After the junction cools to approximately 155°C, the device starts up using the normal start up routine. This feature is provided to prevent catastrophic failures from accidental device overheating. Note that thermal limit will not stop the die from operating above the specified maximum operating temperature, 125°C. The die should be kept under 125°C to ensure correct operation.

8.3.6 Light Load Operation

The LM21215 offers increased efficiency when operating at light loads. Whenever the load current is reduced to a point where the peak to peak inductor ripple current is greater than two times the load current, the device will enter the diode emulation mode preventing significant negative inductor current. The point at which this occurs is the critical conduction boundary and can be calculated by the following equation:

$$I_{\text{BOUNDARY}} = \frac{(V_{\text{IN}} - V_{\text{OUT}}) \times D}{2 \times L \times f_{\text{SW}}} \quad (1)$$

It can be seen that in diode emulation mode, whenever the inductor current reaches zero the SW node becomes high impedance. Ringing will occur on this pin as a result of the LC tank circuit formed by the inductor and the parasitic capacitance at the node. If this ringing is of concern an additional RC snubber circuit can be added from the switch node to ground.

At very light loads, usually below 100 mA, several pulses may be skipped in between switching cycles, effectively reducing the switching frequency and further improving light-load efficiency.

8.3.7 Power Good Flag

The PGOOD pin provides the user with a way to monitor the status of the LM21215. In order to use the PGOOD pin, the application must provide a pullup resistor to a desired DC voltage (in other words, V_{IN}). PGOOD will respond to a fault condition by pulling the PGOOD pin low with the open-drain output. PGOOD pulls low on the following conditions: 1) V_{FB} moves above or below the V_{OVP} or V_{UVP} , respectively 2) The enable pin (EN) is brought below the enable threshold 3) The device enters a pre-biased output condition ($V_{\text{FB}} > V_{\text{SS}}$).

Figure 21 shows the conditions that will cause PGOOD to fall.

Feature Description (continued)

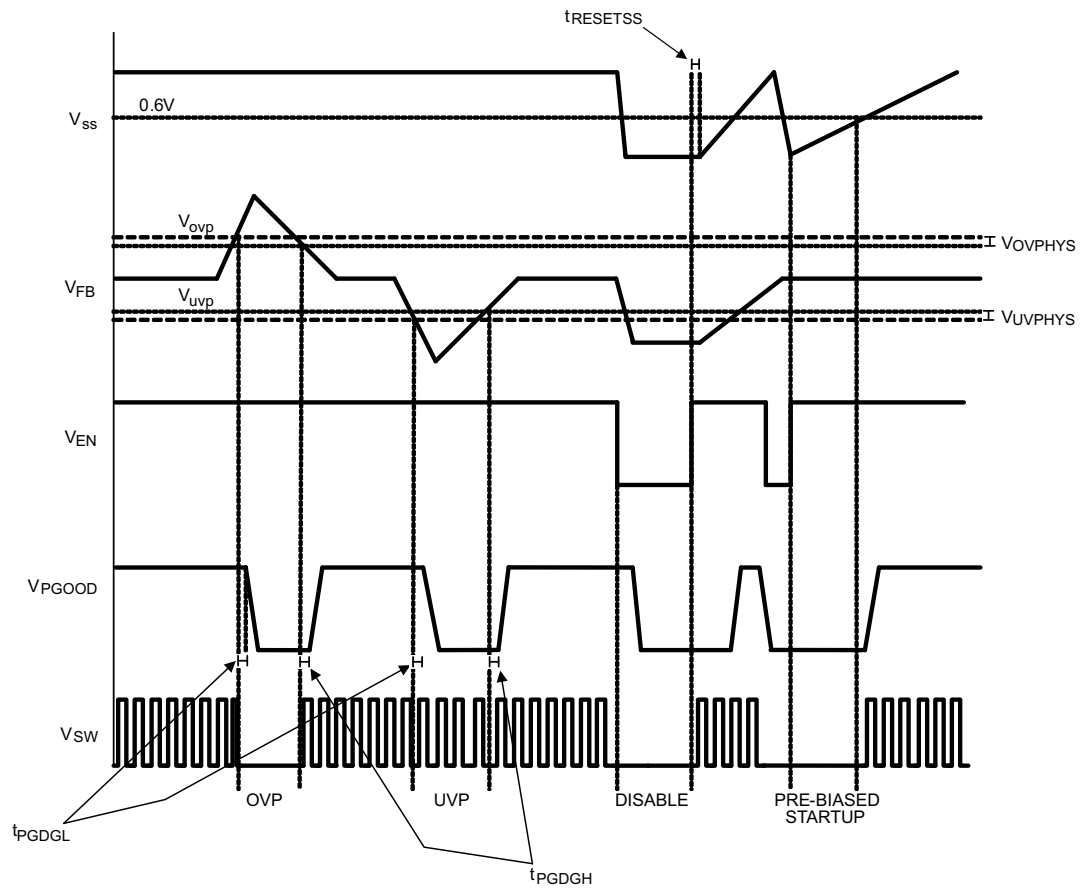


Figure 21. PGOOD Conditions

8.4 Device Functional Modes

Several diagrams are shown in illustrating continuous conduction mode (CCM), discontinuous conduction mode (DCM), and the boundary condition.

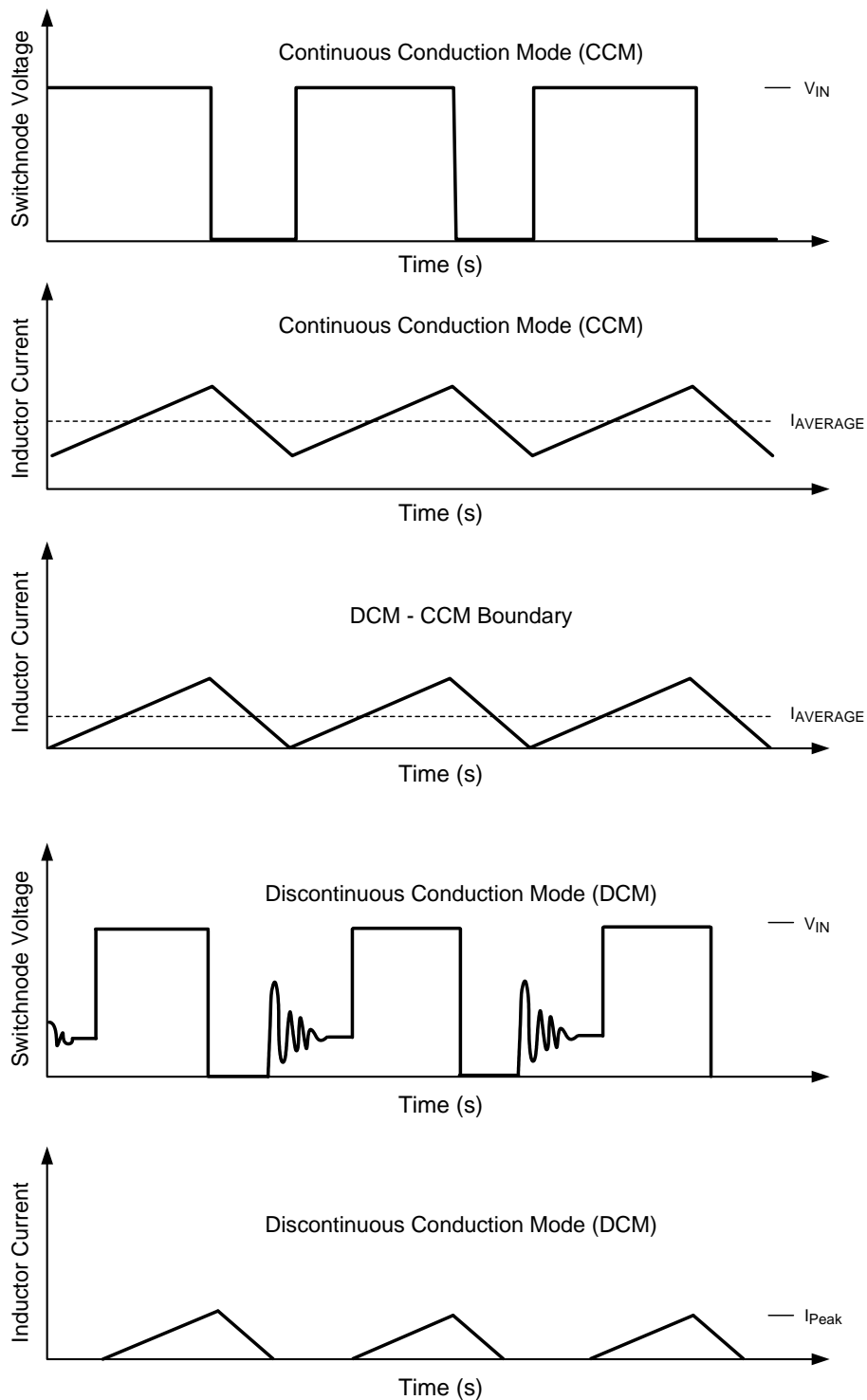


Figure 22. Modes Of Operation for LM21215

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LM21212-2 switching regulator features all of the functions necessary to implement an efficient low voltage buck regulator using a minimum number of external components. This easy-to-use regulator features two integrated switches and is capable of supplying up to 12 A of continuous output current. The regulator utilizes voltage mode control with trailing edge modulation to optimize stability and transient response over the entire output voltage range. The device can operate at high switching frequency allowing use of a small inductor while still achieving high efficiency.

9.2 Typical Application

9.2.1 Typical Application 1

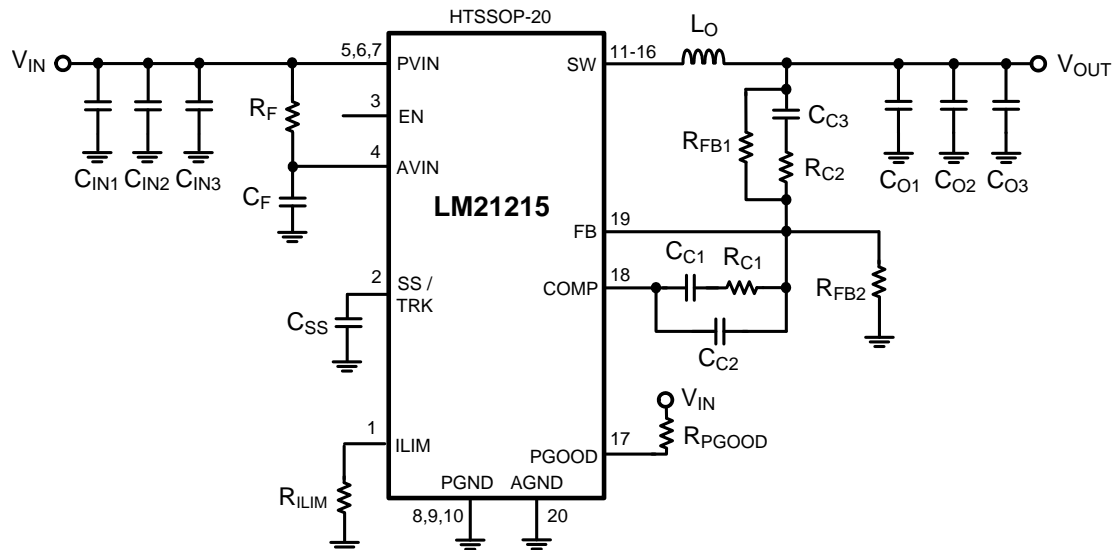


Figure 23. Typical Application Schematic 1

Typical Application (continued)

9.2.1.1 Design Requirements

Table 1. Bill Of Materials ($V_{IN} = 3.3\text{ V}$ - 5.5 V , $V_{OUT} = 1.2\text{ V}$, $I_{OUT} = 15\text{ A}$)

ID	DESCRIPTION	VENDOR	PART NUMBER	QUANTITY
C_F	CAP, CERM, 1uF, 10V, +/-10%, X7R, 0603	MuRata	GRM188R71A105KA61D	1
$C_{IN1}, C_{IN2},$ $C_{IN3}, C_{O1}, C_{O2},$ C_{O3}	CAP, CERM, 100uF, 6.3V, +/-20%, X5R, 1206	MuRata	GRM31CR60J107ME39L	6
C_{C1}	CAP, CERM, 1800pF, 50V, +/-5%, C0G/NP0, 0603	TDK	C1608C0G1H182J	1
C_{C2}	CAP, CERM, 68pF, 50V, +/-5%, C0G/NP0, 0603	TDK	C1608C0G1H680J	1
C_{C3}	CAP, CERM, 820pF, 50V, +/-5%, C0G/NP0, 0603	TDK	C1608C0G1H821J	1
C_{SS}	CAP, CERM, 0.033uF, 16V, +/-10%, X7R, 0603	MuRata	GRM188R71C333KA01D	1
L_O	Inductor, Shielded Drum Core, Powdered Iron, 560nH, 27.5A, 0.0018 ohm, SMD	Vishay-Dale	IHLP4040DZERR56M01	1
R_F	RES, 1.0 ohm, 5%, 0.1W, 0603	Vishay-Dale	CRCW06031R00JNEA	1
R_{C1}	RES, 9.31k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW06039K31FKEA	1
R_{C2}	RES, 165 ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW0603165RFKEA	1
$R_{FB1}, R_{FB2},$ R_{PGOOD}	RES, 10k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW060310K0FKEA	3
R_{ILIM}	RES, 7.15k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW06037K15FKEA	1

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Custom Design With WEBENCH® Tools

[Click here](#) to create a custom design using the LM21215 device with the WEBENCH® Power Designer.

1. Start by entering the input voltage (V_{IN}), output voltage (V_{OUT}), and output current (I_{OUT}) requirements.
2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at www.ti.com/WEBENCH.

9.2.1.2.2 Output Voltage

The first step in designing the LM21215 application is setting the output voltage. This is done by using a voltage divider between V_{OUT} and AGND, with the middle node connected to V_{FB} . When operating under steady-state conditions, the LM21215 forces V_{OUT} so that V_{FB} is driven to 0.6 V.

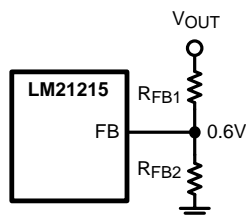


Figure 24. Setting V_{OUT}

A good starting point for the lower feedback resistor, R_{FB2} , is 10 k Ω . R_{FB1} can then be calculated with [Equation 2](#):

$$V_{OUT} = \frac{R_{FB1} + R_{FB2}}{R_{FB2}} 0.6V \quad (2)$$

9.2.1.2.3 Precision Enable

The enable (EN) pin of the LM21215 allows the output to be toggled on and off. This pin is a precision analog input. When the voltage exceeds 1.35 V, the controller will try to regulate the output voltage as long as the input voltage has exceeded the UVLO voltage of 2.7 V. There is an internal current source connected to EN so if enable is not used, the device will turn on automatically. If EN is not toggled directly the device can be preprogrammed to turn on at a certain input voltage higher than the UVLO voltage. This can be done with an external resistor divider from AVIN to EN and EN to AGND as shown below in [Figure 25](#).

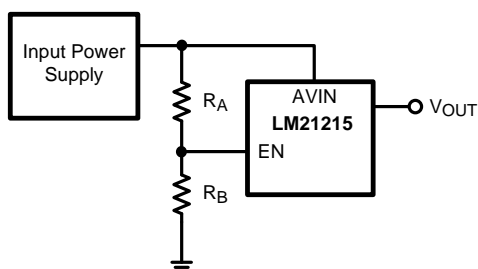


Figure 25. Enable Startup Through V_{IN}

The resistor values of R_A and R_B can be relatively sized to allow EN to reach the enable threshold voltage depending on the input supply voltage. With the enable current source accounted for, the equation solving for R_A is the following:

$$R_A = \frac{R_B(V_{PVIN} - 1.35V)}{1.35V - I_{EN}R_B}$$

where

- R_A is the resistor from V_{IN} to enable
 - R_B is the resistor from enable to ground
 - I_{EN} is the internal enable pullup current (2 μA)
 - 1.35 V is the fixed precision enable threshold voltage
- (3)

Typical values for R_B range from 10 k Ω to 100 k Ω .

9.2.1.2.4 Soft Start

When EN has exceeded 1.35 V, and both PVIN and AVIN have exceeded the UVLO threshold, the LM21215 begins charging the output linearly to the voltage level dictated by the feedback resistor network. The LM21215 employs a user adjustable soft start circuit to lengthen the charging time of the output set by a capacitor from the soft start pin to ground. After enable exceeds 1.35 V, an internal 2- μA current source begins to charge the soft start capacitor. This allows the user to limit inrush currents due to a high output capacitance and not cause an overcurrent condition. Adding a soft-start capacitor can also reduce the stress on the input rail. Larger capacitor values will result in longer startup times. Use [Equation 4](#) to approximate the size of the soft-start capacitor:

$$\frac{t_{SS} \times I_{SS}}{0.6V} = C_{SS}$$

where

- I_{SS} is nominally 2 μA
 - t_{SS} is the desired startup time
- (4)

If V_{IN} is higher than the UVLO level and enable is toggled high the soft start sequence begins. There is a small delay between enable transitioning high and the beginning of the soft start sequence. This delay allows the LM21215 to initialize its internal circuitry. Once the output has charged to 90% of the nominal output voltage the power-good flag transitions high. This behavior is illustrated in Figure 26.

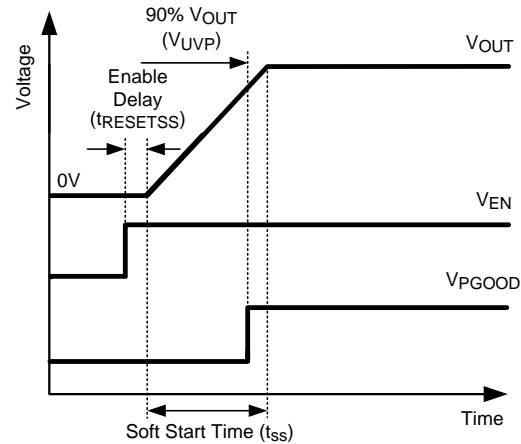


Figure 26. Soft-Start Timing

As shown above, the size of the capacitor is influenced by the nominal feedback voltage level 0.6 V, the soft-start charging current I_{SS} (2 μ A), and the desired soft-start time. If no soft-start capacitor is used then the LM21215 defaults to a minimum startup time of 500 μ s. The LM21215 does not start up faster than 500 μ s. When enable is cycled or the device enters UVLO, the charge developed on the soft-start capacitor is discharged to reset the start-up process. This also happens when the device enters short circuit mode from an overcurrent event.

9.2.1.2.5 Inductor Selection

The inductor (L) used in the application influences the ripple current and the efficiency of the system. The first selection criteria is to define a ripple current, ΔI_L . In a buck converter, it is typically selected to run between 20% to 30% of the maximum output current. Figure 27 shows the ripple current in a standard buck converter operating in continuous conduction mode. Larger ripple current results in a smaller inductance value, which will lead to a lower series resistance in the inductor, and improved efficiency. However, larger ripple current will also cause the device to operate in discontinuous conduction mode at a higher average output current.

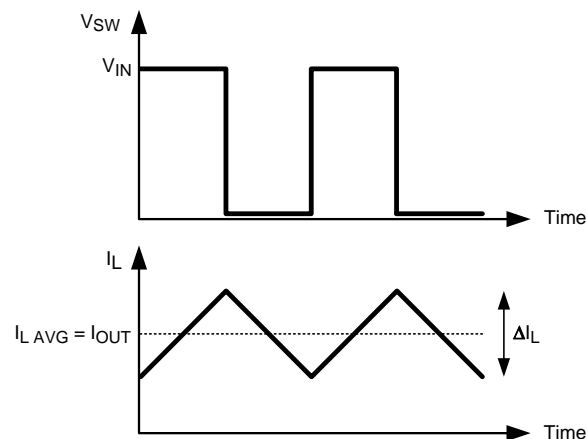


Figure 27. Switch And Inductor Current Waveforms

Once the ripple current has been determined, the appropriate inductor size can be calculated using the following equation:

$$L = \frac{(V_{IN} - V_{OUT}) \cdot D}{\Delta I_L \cdot f_{SW}} \quad (5)$$

9.2.1.2.6 Output Capacitor Selection

The output capacitor, C_{OUT} , filters the inductor ripple current and provides a source of charge for transient load conditions. A wide range of output capacitors may be used with the LM21215 that provide various advantages. The best performance is typically obtained using ceramic, SP or OSCON type chemistries. Typical trade-offs are that the ceramic capacitor provides extremely low ESR to reduce the output ripple voltage and noise spikes, while the SP and OSCON capacitors provide a large bulk capacitance in a small volume for transient loading conditions.

When selecting the value for the output capacitor, the two performance characteristics to consider are the output voltage ripple and transient response. The output voltage ripple can be approximated by using [Equation 6](#):

$$\Delta V_{OUT} \approx \Delta I_L \times \left[R_{ESR} + \frac{1}{8 \times f_{SW} \times C_{OUT}} \right]$$

where

- ΔV_{OUT} (V) is the amount of peak-to-peak voltage ripple at the power supply output
 - R_{ESR} (Ω) is the series resistance of the output capacitor
 - f_{SW} (Hz) is the switching frequency
 - C_{OUT} (F) is the output capacitance used in the design
- (6)

The amount of output ripple that can be tolerated is application specific; however a general recommendation is to keep the output ripple less than 1% of the rated output voltage. Keep in mind ceramic capacitors are sometimes preferred because they have very low ESR; however, depending on package and voltage rating of the capacitor the value of the capacitance can drop significantly with applied voltage. The output capacitor selection will also affect the output voltage droop during a load transient. The peak droop on the output voltage during a load transient is dependent on many factors; however, an approximation of the transient droop ignoring loop bandwidth can be obtained using [Equation 7](#):

$$V_{\text{DROOP}} = \Delta I_{\text{OUTSTEP}} \times R_{\text{ESR}} + \frac{L \times \Delta I_{\text{OUTSTEP}}^2}{C_{\text{OUT}} \times (V_{\text{IN}} - V_{\text{OUT}})}$$

where

- C_{OUT} (F) is the minimum required output capacitance
- L (H) is the value of the inductor
- V_{DROOP} (V) is the output voltage drop ignoring loop bandwidth considerations
- $\Delta I_{\text{OUTSTEP}}$ (A) is the load step change
- R_{ESR} (Ω) is the output capacitor ESR
- V_{IN} (V) is the input voltage
- V_{OUT} (V) is the set regulator output voltage

(7)

Examine both the tolerance and voltage coefficient of the capacitor when designing for a specific output ripple or transient droop target.

9.2.1.2.7 Input Capacitor Selection

Quality input capacitors are necessary to limit the ripple voltage at the VIN pin while supplying most of the switch current during the on-time. Additionally, they help minimize input voltage droop in an output current transient condition. In general, it is recommended to use a ceramic capacitor for the input as it provides both a low impedance and small footprint. Use of a high grade dielectric for the ceramic capacitor, such as X5R or X7R, will provide improved overtemperature performance and also minimize the DC voltage derating that occurs with Y5V capacitors. The input capacitors C_{IN1} and C_{IN2} must be placed as close as possible to the PVIN and PGND pins.

Select non-ceramic input capacitors for RMS current rating and minimum ripple voltage. A good approximation for the required ripple current rating is given by the relationship:

$$I_{\text{IN-RMS}} = I_{\text{OUT}} \sqrt{D(1 - D)}$$

(8)

As indicated by the RMS ripple current equation, highest requirement for RMS current rating occurs at 50% duty cycle. For this case, the RMS ripple current rating of the input capacitor should be greater than half the output current. For best performance, low ESR ceramic capacitors should be placed in parallel with higher capacitance capacitors to provide the best input filtering for the device.

When operating at low input voltages (3.3 V or lower), additional capacitance may be necessary to protect from triggering an under-voltage condition on an output current transient. This will depend on the impedance between the input voltage supply and the LM21215, as well as the magnitude and slew rate of the output transient.

The AVIN pin requires a 1- μ F ceramic capacitor to AGND and a 1- Ω resistor to PVIN. This RC network filters inherent noise on PVIN from the sensitive analog circuitry connected to AVIN.

9.2.1.2.8 Programmable Current Limit

A resistor from the ILIM pin to GND sets the internal current limit on the LM21215. Program the current limit so that the peak inductor current (I_L) does not trigger the current limit in normal operation. This requires setting the resistor from the ILIM pin to GND (R_{ILIM}) to the appropriate value to allow the maximum ripple current, ΔI_{LMAX} plus the DC output current through the high-side FET during normal operation. The maximum ripple current can be described as:

For $D > 0.5$

$$\Delta I_{\text{LMAX}} = \frac{(V_{\text{INMAX}} - V_{\text{OUTMIN}}) \cdot V_{\text{OUTMIN}}}{L_{\text{MIN}} \cdot f_{\text{SWMIN}} \cdot V_{\text{INMAX}}}$$

For $D < 0.5$

$$\Delta I_{\text{LMAX}} = \frac{(V_{\text{INMIN}} - V_{\text{OUTMAX}}) \cdot V_{\text{OUTMAX}}}{L_{\text{MIN}} \cdot f_{\text{SWMIN}} \cdot V_{\text{INMIN}}}$$

where

- V_{INMAX} , V_{INMIN} , V_{OUTMAX} , V_{OUTMIN} , L_{MIN} and F_{SWMIN} are the respective maximum and minimum conditions of the system as defined by the component tolerance and device variation

(9)

From this, the maximum allowable current through the high-side FET (I_{HSMAX}) of device can be described as:

$$I_{HSMAX} = \frac{\Delta I_{LMAX}}{2} + I_{DCMAX}$$

where

- I_{OUTMAX} is the maximum defined DC output current, up to 15 A

(10)

Once the I_{HSMAX} value has been determined, a nominal value of the R_{ILIM} resistor can be calculated as follows:

$$R_{ILIM} (k\Omega) = \frac{582.4}{I_{HSMAX}} - 14.2$$

where

- R_{ILIM} value is the nominal resistance necessary for the given I_{HSMAX} value

(11)

A conservative design should also take into account the device variation over V_{IN} and temperature, as seen in [Electrical Characteristics](#) for the I_{CLR} parameter and the typical performance characteristics. These variations can cause the I_{HSMAX} value to increase, depending on the range of the input voltage and junction temperature.

9.2.1.2.9 Control Loop Compensation

The LM21215 incorporates a high bandwidth amplifier between the FB and COMP pins to allow the user to design a compensation network that matches the application. This section will walk through the various steps in obtaining the open loop transfer function.

There are three main blocks of a voltage mode buck converter that the power supply designer must consider when designing the control system; the power train, modulator, and the compensated error amplifier. A closed loop diagram is shown in [Figure 28](#).

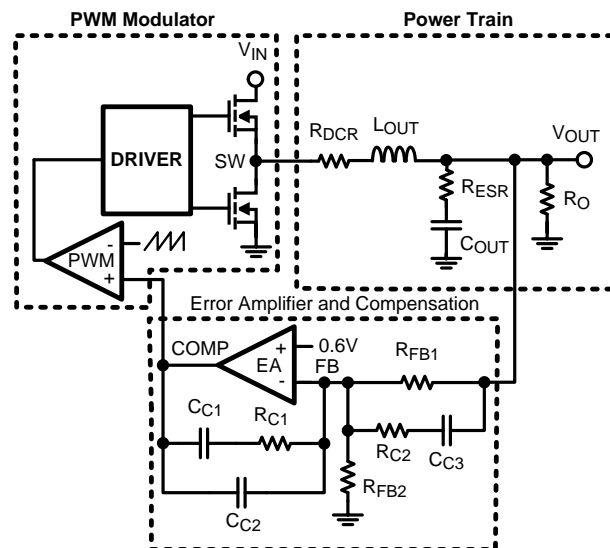


Figure 28. Loop Diagram

The power train consists of the output inductor (L) with DCR (DC resistance R_{DCR}), output capacitor (C_0) with ESR (effective series resistance R_{ESR}), and load resistance (R_o). The error amplifier (EA) constantly forces FB to 0.6V. The passive compensation components around the error amplifier help maintain system stability. The modulator creates the duty cycle by comparing the error amplifier signal with an internally generated ramp set at the switching frequency.

There are three transfer functions that must be taken into consideration when obtaining the total open loop transfer function; COMP to SW (modulator), SW to V_{OUT} (power train), and V_{OUT} to COMP (error amplifier). The COMP to SW transfer function is simply the gain of the PWM modulator.

$$G_{PWM} = \frac{V_{in}}{\Delta V_{ramp}}$$

where

- ΔV_{RAMP} is the oscillator peak-to-peak ramp voltage (nominally 0.8 V) (12)

The SW to COMP transfer function includes the output inductor, output capacitor, and output load resistance. The inductor and capacitor create two complex poles at a frequency described by:

$$f_{LC} = \frac{1}{2\pi} \sqrt{\frac{R_O + R_{DCR}}{L_{OUT}C_{OUT}(R_O + R_{ESR})}} \quad (13)$$

In addition to two complex poles, a left half plane zero is created by the output capacitor ESR located at a frequency described by:

$$f_{esr} = \frac{1}{2\pi C_O R_{esr}} \quad (14)$$

A Bode plot showing the power train response can be seen below.

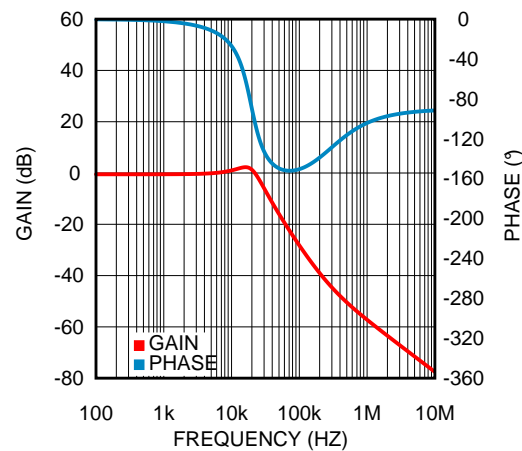
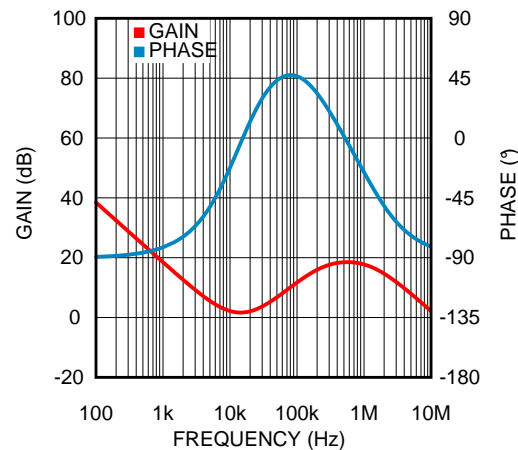


Figure 29. Power Train Bode Plot

The complex poles created by the output inductor and capacitor cause a 180° phase shift at the resonant frequency as seen in Figure 29. The phase is boosted back up to -90° due to the output capacitor ESR zero. The 180° phase shift must be compensated out and phase boosted through the error amplifier to stabilize the closed loop response. The compensation network shown around the error amplifier in Figure 28 creates two poles, two zeros and a pole at the origin. Placing these poles and zeros at the correct frequencies stabilizes the closed loop response. The Compensated Error Amplifier transfer function is:

$$G_{EA} = K_m \frac{\left(\frac{s}{2\pi f_{Z1}} + 1\right) \left(\frac{s}{2\pi f_{Z2}} + 1\right)}{s \left(\frac{s}{2\pi f_{P1}} + 1\right) \left(\frac{s}{2\pi f_{P2}} + 1\right)} \quad (15)$$

The pole located at the origin gives high open loop gain at DC, translating into improved load regulation accuracy. This pole occurs at a very low frequency due to the limited gain of the error amplifier, however, it can be approximated at DC for the purposes of compensation. The other two poles and two zeros can be located accordingly to stabilize the voltage mode loop depending on the power stage complex poles and Q. Figure 30 is an illustration of what the Error Amplifier Compensation transfer function will look like.


Figure 30. Type 3 Compensation Network Bode Plot

As seen in [Figure 30](#), the two zeros ($f_{LC}/2$, f_{LC}) in the compensation network give a phase boost. This will cancel out the effects of the phase loss from the output filter. The compensation network also adds two poles to the system. One pole should be located at the zero caused by the output capacitor ESR (f_{ESR}), and the other pole must be at half the switching frequency ($f_{SW}/2$) to roll off the high frequency response. The dependency of the pole and zero locations on the compensation components is described below.

$$\begin{aligned}
 f_{Z1} &= \frac{f_{LC}}{2} = \frac{1}{2\pi R_{C1} C_{C1}} \\
 f_{Z2} &= f_{LC} = \frac{1}{2\pi (R_{C1} + R_{FB1}) C_{C3}} \\
 f_{P1} &= f_{ESR} = \frac{1}{2\pi R_{C2} C_{C3}} \\
 f_{P2} &= \frac{f_{SW}}{2} = \frac{C_{C1} + C_{C2}}{2\pi R_{C1} C_{C1} C_{C2}}
 \end{aligned}
 \tag{16}$$

An example of the step-by-step procedure to generate compensation component values using the typical application setup, (see [Figure 30](#)), is given. The parameters needed for the compensation values are given in the table below.

PARAMETER	VALUE
V_{IN}	5 V
V_{OUT}	1.2 V
I_{OUT}	15 A
$f_{CROSSOVER}$	100 kHz
L	0.56 μ H
R_{DCR}	1.8 m Ω
C_O	150 μ F
R_{ESR}	1.0 m Ω
ΔV_{RAMP}	0.8 V
f_{SW}	500 kHz

where ΔV_{RAMP} is the oscillator peak-to-peak ramp voltage (nominally 0.8 V), and $f_{CROSSOVER}$ is the frequency at which the open-loop gain is a magnitude of 1. It is recommended that the $f_{CROSSOVER}$ not exceed one-fifth of the switching frequency. The output capacitance, C_O , depends on capacitor chemistry and bias voltage. For multi-layer ceramic capacitors (MLCC), the total capacitance will degrade as the DC bias voltage is increased. Measuring the actual capacitance value for the output capacitors at the output voltage is recommended to

accurately calculate the compensation network. The example given here is the total output capacitance using the three MLCC output capacitors biased at 1.2V, as seen in the typical application schematic, . Note that it is more conservative, from a stability standpoint, to err on the side of a smaller output capacitance value in the compensation calculations rather than a larger, as this will result in a lower bandwidth but increased phase margin.

First, a the value of R_{FB1} should be chosen. A typical value is 10 k Ω . From this, the value of R_{C1} can be calculated to set the mid-band gain so that the desired crossover frequency is achieved:

$$\begin{aligned} R_{C1} &= \frac{f_{\text{crossover}}}{f_{LC}} \cdot \frac{\Delta V_{\text{RAMP}}}{V_{IN}} \cdot R_{FB1} \\ &= \frac{100 \text{ kHz}}{17.4 \text{ kHz}} \cdot \frac{0.8 \text{ V}}{5.0 \text{ V}} \cdot 10 \text{ k}\Omega \\ &= 9.2 \text{ k}\Omega \end{aligned} \quad (17)$$

Next, the value of C_{C1} can be calculated by placing a zero at half of the LC double pole frequency (f_{LC}):

$$\begin{aligned} C_{C1} &= \frac{1}{\pi f_{LC} R_{C1}} \\ &= 1.99 \text{ nF} \end{aligned} \quad (18)$$

Now the value of C_{C2} can be calculated to place a pole at half of the switching frequency (f_{SW}):

$$\begin{aligned} C_{C2} &= \frac{C_{C1}}{\pi f_{SW} R_{C1} C_{C1} - 1} \\ &= 71 \text{ pF} \end{aligned} \quad (19)$$

R_{C2} can then be calculated to set the second zero at the LC double pole frequency:

$$\begin{aligned} R_{C2} &= \frac{R_{FB1} f_{LC}}{f_{ESR} - f_{LC}} \\ &= 166\Omega \end{aligned} \quad (20)$$

Last, C_{C3} can be calculated to place a pole at the same frequency as the zero created by the output capacitor ESR:

$$\begin{aligned} C_{C3} &= \frac{1}{2\pi f_{ESR} R_{C2}} \\ &= 898 \text{ pF} \end{aligned} \quad (21)$$

An illustration of the total loop response can be seen in [Figure 31](#).

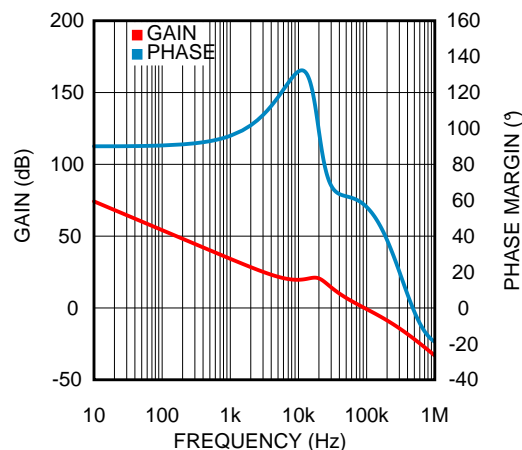


Figure 31. Loop Response

It is important to verify the stability by either observing the load transient response or by using a network analyzer. A phase margin between 45° and 70° is usually desired for voltage mode systems. Excessive phase margin can cause slow system response to load transients and low phase margin may cause an oscillatory load transient response. If the load step response peak deviation is larger than desired, increasing $f_{\text{CROSSOVER}}$ and recalculating the compensation components may help but usually at the expense of phase margin.

9.2.1.3 Application Curves

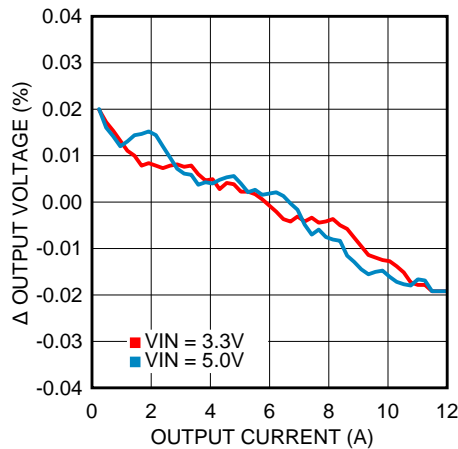


Figure 32. Load Regulation

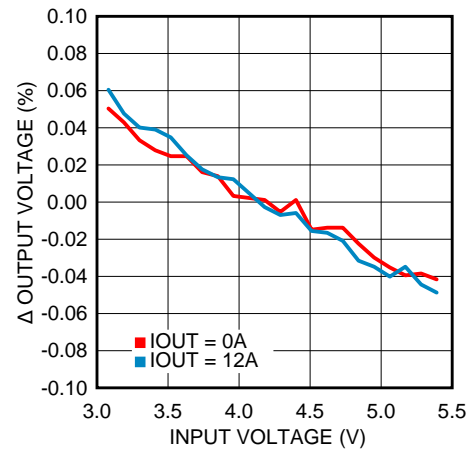


Figure 33. Line Regulation

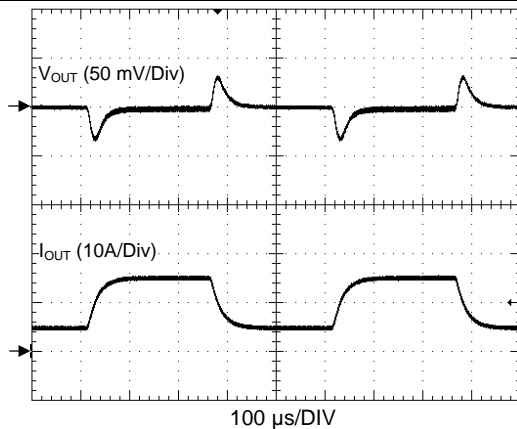


Figure 34. Load Transient Response

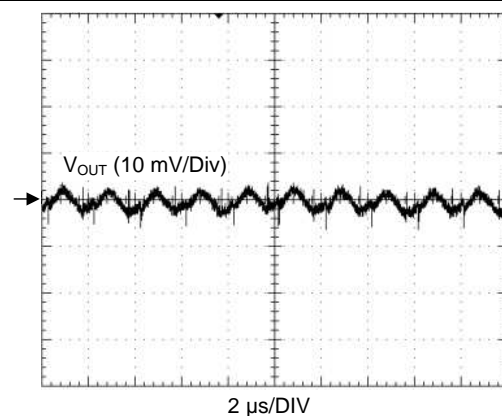


Figure 35. Output Voltage Ripple ($I_{\text{OUT}} = 15$ A)

9.2.2 Typical Application Schematic 2

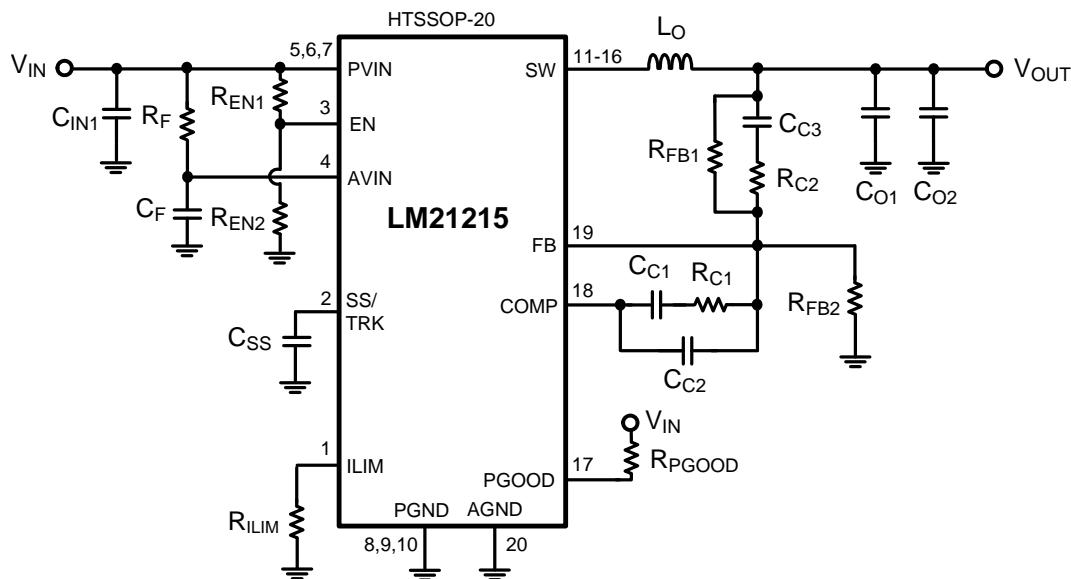


Figure 36. Typical Application Schematic 2

9.2.2.1 Design Requirements

Table 2. Bill Of Materials ($V_{IN} = 4\text{ V to }5.5\text{ V}$, $V_{OUT} = 0.9\text{ V}$, $I_{OUT} = 8\text{ A}$)

ID	DESCRIPTION	VENDOR	PART NUMBER	QUANTITY
C_F	CAP, CERM, 1uF, 10V, +/-10%, X7R, 0603	MuRata	GRM188R71A105KA61D	1
C_{IN1} , C_{O1} , C_{O2}	CAP, CERM, 100uF, 6.3V, +/-20%, X5R, 1206	MuRata	GRM31CR60J107ME39L	3
C_{C1}	CAP, CERM, 1800pF, 50V, +/-5%, C0G/NP0, 0603	MuRata	GRM1885C1H182JA01D	1
C_{C2}	CAP, CERM, 82pF, 50V, +/-5%, C0G/NP0, 0603	TDK	C1608C0G1H820J	1
C_{C3}	CAP, CERM, 820pF, 50V, +/-5%, C0G/NP0, 0603	TDK	C1608C0G1H821J	1
C_{SS}	CAP, CERM, 0.033uF, 16V, +/-10%, X7R, 0603	MuRata	GRM188R71C333KA01D	1
L_O	Inductor, Shielded Drum Core, 680nH, 22A, 0.0014 ohm, SMD	Coilcraft	XAL1060-681ME	1
R_F	RES, 1.0 ohm, 5%, 0.1W, 0603	Vishay-Dale	CRCW06031R00JNEA	1
R_{C1}	RES, 8.25k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW06038K25FKEA	1
R_{C2}	RES, 124 ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW0603124RFKEA	1
R_{EN1} , R_{FB1} , R_{PGOOD}	RES, 10k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW060310K0FKEA	3
R_{EN2}	RES, 19.6k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW060319K6FKEA	1
R_{FB2}	RES, 20.0k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW060320K0FKEA	1
R_{ILIM}	RES, 39.2k ohm, 1%, 0.1W, 0603	Vishay-Dale	CRCW060339K2FKEA	1

9.2.2.2 Detailed Design Procedure

See [Detailed Design Procedure](#)

10 Layout

10.1 Layout Considerations

PC board layout is an important part of DC/DC converter design. Poor board layout can disrupt the performance of a DC/DC converter and surrounding circuitry by contributing to EMI, ground bounce, and resistive voltage loss in the traces. These can send erroneous signals to the DC/DC converter resulting in poor regulation or instability.

Good layout can be implemented by following a few simple design rules.

1. Minimize area of switched current loops. In a buck regulator there are two loops where currents are switched at high slew rates. The first loop starts from the input capacitor, to the regulator PVIN pin, to the regulator SW pin, to the inductor then out to the output capacitor and load. The second loop starts from the output capacitor ground, to the regulator GND pins, to the inductor and then out to the load (see [Figure 37](#)). To minimize both loop areas, place the input capacitor as close as possible to the VIN pin. Grounding for both the input and output capacitor must be close. Ideally, a ground plane should be placed on the top layer that connects the PGND pins, the exposed pad (EP) of the device, and the ground connections of the input and output capacitors in a small area near pin 10 and 11 of the device. The inductor should be placed as close as possible to the SW pin and output capacitor.
2. Minimize the copper area of the switch node. Route the six SW pins on a single top plane to the pad of the inductor. Place the inductor should be placed to the switch pins of the device with a wide trace to minimize conductive losses. The inductor can be placed on the bottom side of the PCB relative to the LM21215, but care must be taken to not allow any coupling of the magnetic field of the inductor into the sensitive feedback or compensation traces.
3. Have a solid ground plane between PGND, the EP and the input and output capacitor ground connections. The ground connections for the AGND, compensation, feedback, and soft-start components should be physically isolated (located near pin 1 and 20) from the power ground plane but a separate ground connection is not necessary. If not properly handled, poor grounding can result in degraded load regulation or erratic switching behavior.
4. Carefully route the connection from the VOUT signal to the compensation network. This node is high impedance and can be susceptible to noise coupling. The trace should be routed away from the SW pin and inductor to avoid contaminating the feedback signal with switch noise.
5. Make input and output bus connections as wide as possible. This reduces any voltage drops on the input or output of the converter and can improve efficiency. Voltage accuracy at the load is important so make sure feedback voltage sense is made at the load. Doing so corrects for voltage drops at the load and provide the best output accuracy.
6. Provide adequate device heat sinking. For most 15 A designs a four layer board is recommended. Use as many vias as is possible to connect the EP to the power plane heatsink. The vias located underneath the EP wicks solder into them if they are not filled. Complete solder coverage of the EP to the board is required to achieve the θ_{JA} values described in the previous section. Either an adequate amount of solder must be applied to the EP pad to fill the vias, or the vias must be filled during manufacturing. See the [Thermal Considerations](#) section to ensure enough copper heatsinking area is used to keep the junction temperature below 125°C.

10.2 Layout Example

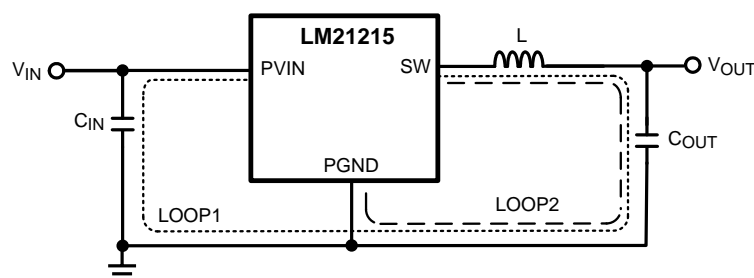


Figure 37. Schematic of LM21215 Highlighting Layout Sensitive Nodes

10.3 Thermal Considerations

The thermal characteristics of the LM21215 are specified using the parameter θ_{JA} , which relates the junction temperature to the ambient temperature. Although the value of θ_{JA} is dependant on many variables, it still can be used to approximate the operating junction temperature of the device.

To obtain an estimate of the device junction temperature, one may use the following relationship:

$$T_J = P_D \cdot \theta_{JA} + T_A \quad (22)$$

and

$$P_D = P_{IN} \cdot (1 - \text{Efficiency}) - I_{OUT}^2 \cdot R_{DCR}$$

where

- T_J is the junction temperature in °C
 - P_{IN} is the input power in Watts ($P_{IN} = V_{IN} \times I_{IN}$)
 - θ_{JA} is the junction to ambient thermal resistance for the LM21215
 - T_A is the ambient temperature in °C
 - I_{OUT} is the output load current in A
- (23)

It is important to always keep the operating junction temperature (T_J) below 125°C for reliable operation. If the junction temperature exceeds 165°C the device cycles in and out of thermal shutdown. If thermal shutdown occurs it is a sign of inadequate heat sinking or excessive power dissipation in the device.

Figure 38, shown below, provides a better approximation of the θ_{JA} for a given PCB copper area. The PCB used in this test consisted of 4 layers: 1oz. copper was used for the internal layers while the external layers were plated to 2 oz. copper weight. To provide an optimal thermal connection, a 3 × 5 array of 8 mil. vias under the thermal pad were used, and an additional twelve 8 mil. vias under the rest of the device were used to connect the 4 layers.

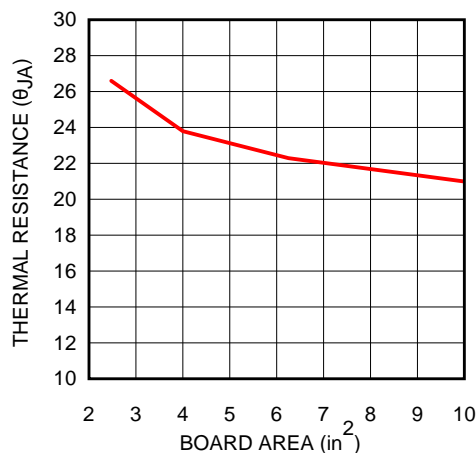


Figure 38. Thermal Resistance vs PCB Area (4-Layer Board)

Thermal Considerations (continued)

Figure 39 shows a plot of the maximum ambient temperature vs output current for the typical application circuit shown in Figure 23, assuming a θ_{JA} value of 24°C/W.

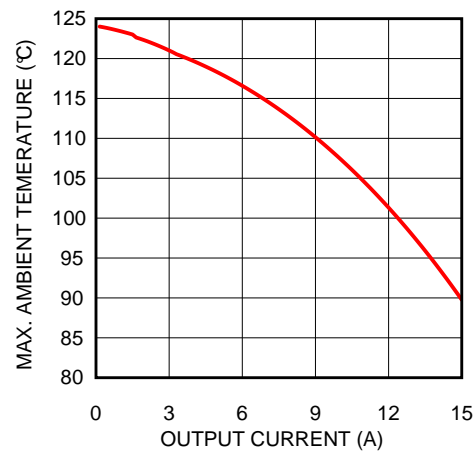


Figure 39. Maximum Ambient Temperature vs Output Current (0 LFM)

11 器件和文档支持

11.1 器件支持

11.1.1 第三方产品免责声明

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11.1.2 开发支持

11.1.2.1 使用 **WEBENCH®** 工具创建定制设计

单击[此处](#)，使用 LM21215 器件并借助 WEBENCH® 电源设计器创建定制设计方案。

1. 首先输入输入电压 (V_{IN})、输出电压 (V_{OUT}) 和输出电流 (I_{OUT}) 要求。
2. 使用优化器拨盘优化该设计的关键参数，如效率、尺寸和成本。
3. 将生成的设计与德州仪器 (TI) 的其他可行的解决方案进行比较。

WEBENCH 电源设计器可提供定制原理图以及罗列实时价格和组件供货情况的物料清单。

在多数情况下，可执行以下操作：

- 运行电气仿真，观察重要波形以及电路性能
- 运行热性能仿真，了解电路板热性能
- 将定制原理图和布局方案以常用 CAD 格式导出
- 打印设计方案的 PDF 报告并与同事共享

有关 WEBENCH 工具的详细信息，请访问 www.ti.com.cn/WEBENCH。

11.2 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的通知我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

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TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM21215MH/NOPB	ACTIVE	HTSSOP	PWP	20	73	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM21215 MH	Samples
LM21215MHE/NOPB	ACTIVE	HTSSOP	PWP	20	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM21215 MH	Samples
LM21215MHX/NOPB	ACTIVE	HTSSOP	PWP	20	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM21215 MH	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM21215MHE/NOPB	HTSSOP	PWP	20	250	178.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
LM21215MHX/NOPB	HTSSOP	PWP	20	2500	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM21215MHE/NOPB	HTSSOP	PWP	20	250	210.0	185.0	35.0
LM21215MHX/NOPB	HTSSOP	PWP	20	2500	367.0	367.0	35.0

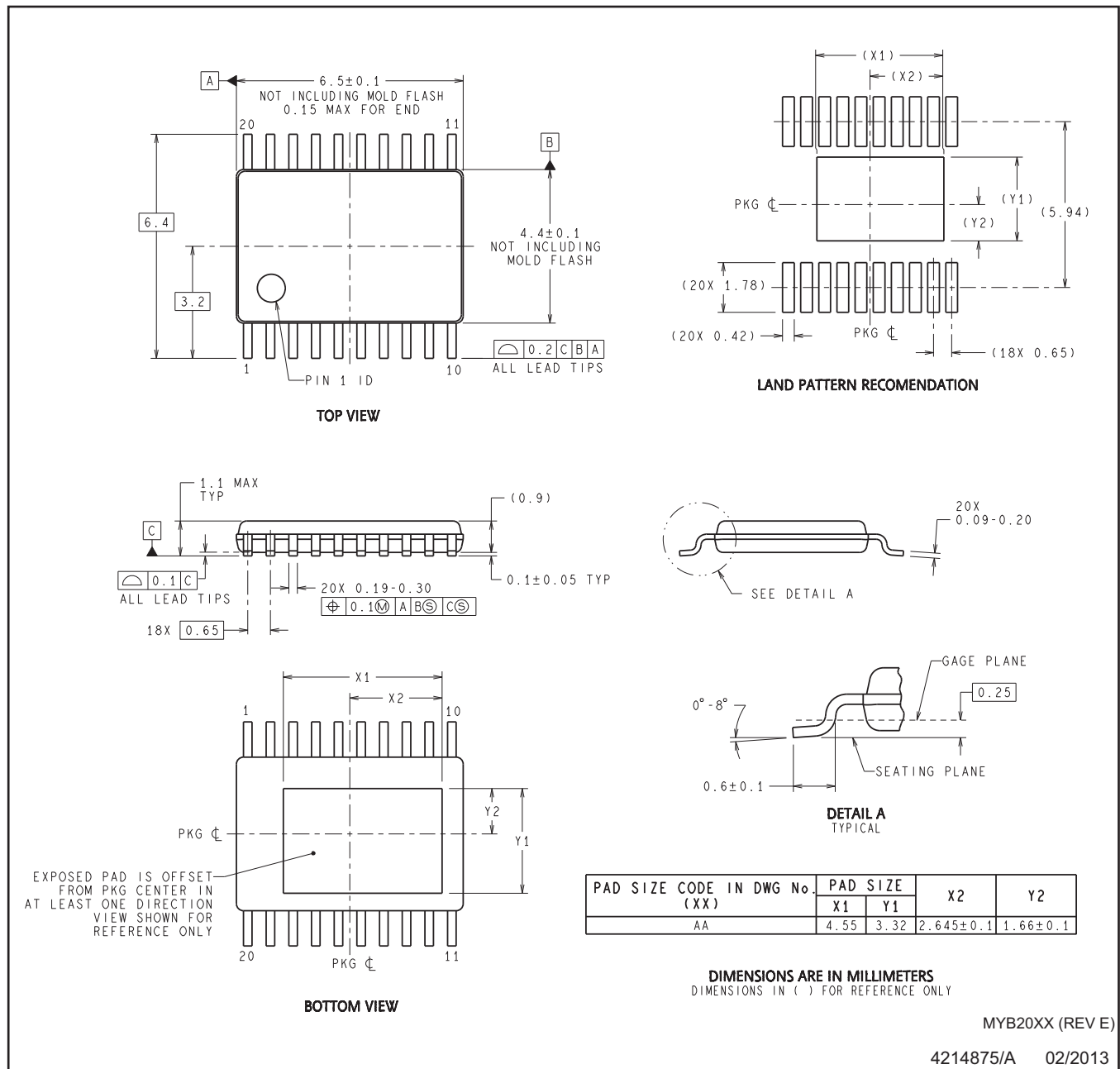
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
LM21215MH/NOPB	PWP	HTSSOP	20	73	495	8	2514.6	4.06

PWP0020AA



- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.
C. Reference JEDEC Registration MO-153, Variation ACT.

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